

IN THE SPECIFICATION

Please replace the third paragraph on page 3 of the specification, beginning at line 12 and ending at line 23, with the following paragraph:

a' Fig. 1 is a schematic view showing one example of a structure of a pulse laser beam irradiator. A laser beam (1106) supplied from a pulse laser beam source (1101) reaches a silicon thin film (1107) on a glass substrate (118) as an irradiated object through an optical path defined by optical devices such as mirrors (1102, 1103, 1105) and a beam homogenizer (1104) installed for homogenizing a spatial intensity. Generally, since one irradiation range is small, a laser beam irradiation is carried out at a desired position on the glass substrate by moving the substrate on an x-y stage (1109). There is also a method of moving the optical devices or combining the optical devices with the stage instead of moving the x-y stage.

IN THE CLAIMS

Please amend the following claims:

- SUB B1 >
- a2
1. (~~Amended~~) A method for forming a first-property semiconductor film at a desired position on a substrate, comprising the steps of:
- preparing the substrate having a second-property semiconductor film formed thereon;
 - preparing an optical mask having a predetermined pattern;
 - relatively positioning a projection area of the optical mask at the desired position on the substrate;
 - irradiating the desired position of the second-property semiconductor film with laser light through the optical mask to change an irradiated portion of the second-property semiconductor film to the first-property semiconductor film; and
 - forming an insulation film on the first-property semiconductor film and the second-property semiconductor film.